

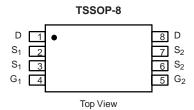
Dual N-Channel 25-V (D-S) MOSFET

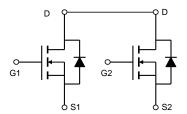
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
25	0.022 at $V_{GS} = 4.5 \text{ V}$	6.6		
	0.032 at V _{GS} = 2.5 V	5.5		

FEATURES

- Halogen-free Option Available
- TrenchFET® Power MOSFETs







ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	25		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Drain Current /T 150 °C\2	T _A = 25 °C	- I _D	6.6	5.2		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		5.5	3.5	^	
Pulsed Drain Current		I _{DM}	30		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	1.5	1.0		
Mariana Bana Birainatia 3	T _A = 25 °C	- P _D	1.5	1.0	W	
Maximum Power Dissipation ^a	T _A = 70 °C		0.96	0.64	V V	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Тур.	Max.	Unit
Mariana da Arabianta	t ≤ 10 s	R _{thJA}	72	83	°C/W
Maximum Junction-to-Ambient ^a	Steady State		100	120	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	55	70	

Notes:

- a. Surface Mounted on FR4 board, $t \le 10$ s.
- * Pb containing terminations are not RoHS compliant, exemptions may apply.



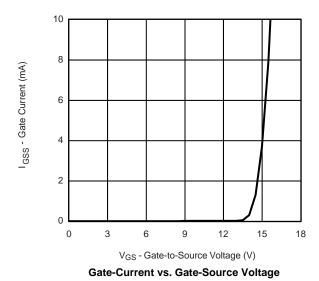
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions M		Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 0.5			1.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 200	nA	
Zoro Coto Voltago Drain Current	I _{DSS}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current		V_{DS} = 25 V, V_{GS} = 0 V, T_{J} = 70 °C			25	μA	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$		0.022		Ω	
		$V_{GS} = 2.5 \text{ V}, I_D = 5.5 \text{ A}$		0.032			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 10 V, I _D = 6.5 A		30		S	
Diode Forward Voltage ^b	V_{SD}	I _S = 1.5 A, V _{GS} = 0 V		0.71	1.2	V	
Dynamic ^a							
Total Gate Charge	Q_g			12	18		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.5 \text{ A}$		2.2		nC	
Gate-Drain Charge	Q _{gd}			3.6			
Turn-On Delay Time	t _{d(on)}			245	365		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		330	495	ne	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_G = 6 Ω		860	1300	ns	
Fall Time	t _f			510	765		

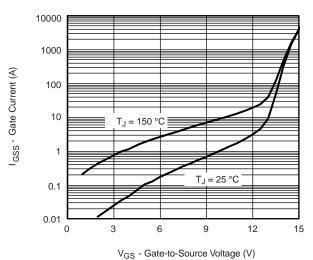
Notes:

- a. For design aid only; not subject to production testing.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

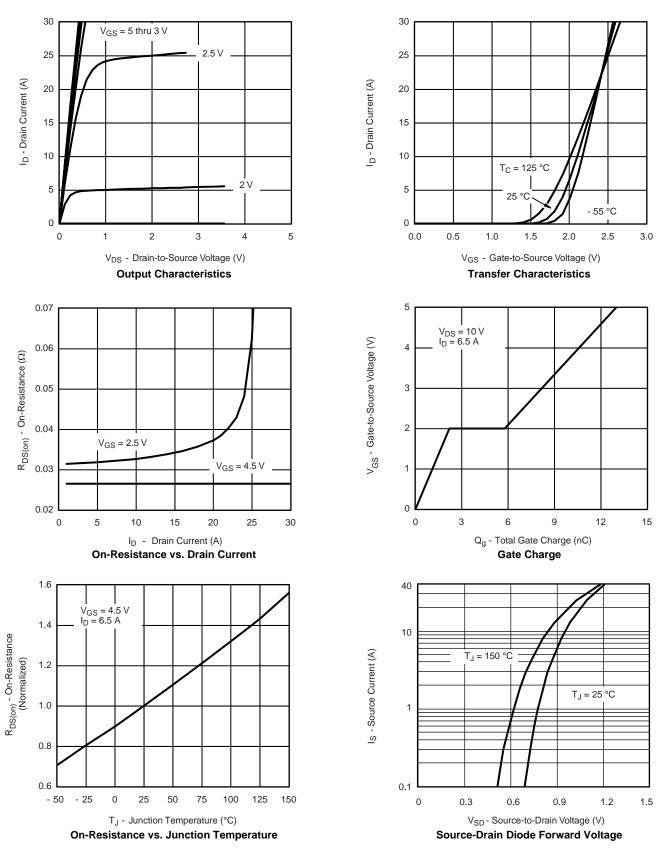




Gate Current vs. Gate-Source Voltage



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





125

10 ms

100 ms I + I + I + I + I

1 s

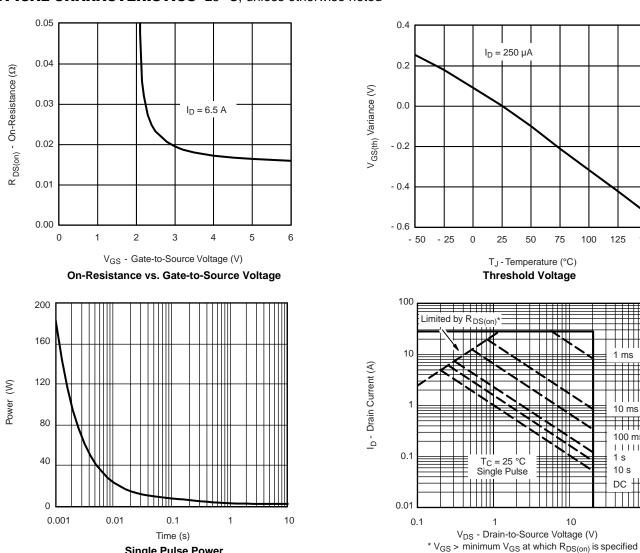
10 s DC #

100

150

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Single Pulse Power

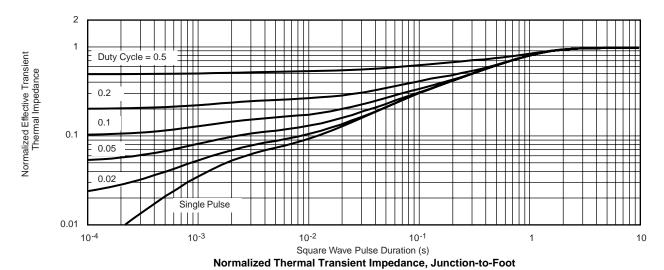




Normalized Thermal Transient Impedance, Junction-to-Ambient



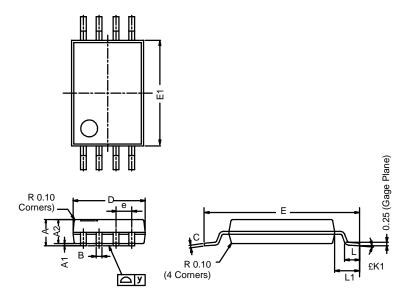
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





TSSOP: 8-LEAD

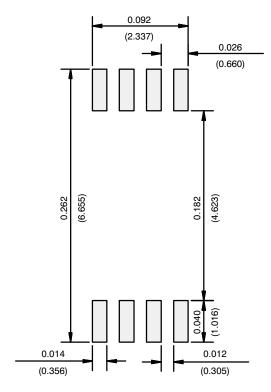
JEDEC Part Number: MO-153



	MILLIMETERS				
Dim	Min	Nom	Max		
Α	-	-	1.20		
A ₁	0.05	0.10	0.15		
A ₂	0.80	1.00	1.05		
В	0.19	0.28	0.30		
С	-	0.127	-		
D	2.90	3.00	3.10		
Е	6.20	6.40	6.60		
E ₁	4.30	4.40	4.50		
е	_	0.65	-		
L	0.45	0.60	0.75		
L ₁	0.90	1.00	1.10		
Y	-	-	0.10		
£K1	0°	3°	6°		
ECN: S-03946—Rev. G, 09-Jul-01 DWG: 5844					



RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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